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**Section I (Amendments to the Claims)**

Please cancel claims 52-120 as set out in the following listing of the claims of the application.

1. (Previously presented) Uncut single crystal III-V nitride material having a large area of at least  $15 \text{ cm}^2$  on a face thereof and having a uniformly low dislocation density not exceeding  $3 \times 10^6$  dislocations per  $\text{cm}^2$  of growth surface area on the face.
2. (Original) Material according to claim 1, selected from the group consisting of AlN, InN, GaN, AlInN, AlInGaN, InGaN, and AlGaN.
3. (Previously presented) Material according to claim 1, wherein the III-V nitride material comprises GaN.
4. (Original) Material according to claim 1, doped with a dopant species.
5. (Original) Material according to claim 4, of a p-doped, n-doped or semi-insulatively doped character.
6. (Original) Material according to claim 3, doped with a dopant species.
7. (Original) Material according to claim 6, wherein the dopant species includes a dopant selected from the group consisting of oxygen and silicon.
8. (Previously presented) Material according to claim 3, having a large area of at least 2 inches in nominal diameter.
9. (Cancelled)
10. (Original) Material according to claim 3, having a thickness of at least 0.1 mm.
11. (Original) Material according to claim 3, having an ADD not exceeding  $2 \times 10^6 \text{ cm}^{-2}$ .
12. (Original) Material according to claim 3, having an ADD not exceeding  $1 \times 10^6 \text{ cm}^{-2}$ .

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13. (Original) Material according to claim 3, having an ADD not exceeding  $5 \times 10^5 \text{ cm}^{-2}$ .
14. (Original) Material according to claim 3, having a DDSDR of less than 50%.
15. (Original) Material according to claim 3, having a DDSDR of less than 25%.
16. (Previously presented) Large area, uniformly low dislocation density single crystal gallium nitride, having a nominal diameter of greater than 2 inches, a thickness of at least 0.1 mm, an ADD not exceeding  $1 \times 10^6 \text{ cm}^{-2}$ , and a DDSDR of less than 25%.
17. (Original) An article, comprising material as claimed in claim 1.
18. (Original) The article of claim 17, wherein said material is on a heteroepitaxial substrate.
19. (Original) The article of claim 18, wherein the heteroepitaxial substrate comprises a material selected from the group consisting of sapphire, silicon carbide, gallium arsenide, silicon, lithium gallate, lithium aluminate, lithium aluminum gallate, zinc oxide, diamond, spinel, and magnesium oxide.
20. (Original) The article of claim 17, wherein said material is GaN.
21. (Original) The article of claim 20, in the form of a crystal having a thickness of at least 50  $\mu\text{m}$ .
22. (Original) The article of claim 21, wherein the thickness of the crystal is greater than 500  $\mu\text{m}$ .
23. (Original) The article of claim 21, wherein the thickness of the crystal is greater than 2 mm.
24. (Original) The article of claim 21, wherein the thickness of the crystal is greater than 10 mm.
25. (Previously presented) The article of claim 21, having a surface including said large area, wherein said surface is at least 2 inches in nominal diameter.
26. (Previously presented) Single crystal III-V nitride material grown exclusively in a bulk growth direction along the c-axis, having a nominal diameter of at least 2 inches, and having uniformly low dislocation density not exceeding  $3 \times 10^6$  dislocations per  $\text{cm}^2$  of growth surface area.

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27. (Previously presented) A wafer comprising the material of claim 26, the wafer having a nominal diameter of from 2 to 8 inches.
28. (Previously presented) A wafer comprising the material of claim 26, the wafer having a rectangular or square shape, with each side at least 15 mm in size.
29. (Previously presented) A wafer comprising the material of claim 26, the wafer having a surface that is parallel to the c-plane of the crystal plane of the single crystal III-V nitride material.
30. (Previously presented) A wafer comprising the material of claim 26, the wafer having a surface disposed at an angle relative to the c-plane of the single crystal III-V nitride material.
31. (Original) The wafer of claim 30, wherein said angle is in a range of from about 0.1 to about 10 degrees.
32. (Previously presented) A wafer comprising the material of claim 26, the wafer having surfaces thereof polished to a mirror finish.
33. (Previously presented) A wafer comprising the material of claim 26, the wafer including a chemical mechanically polished gallium-terminated surface.
34. (Previously presented) A wafer comprising the material of claim 26, wherein the wafer includes a c-plane surface.
35. (Previously presented) A wafer comprising the material of claim 26, wherein the wafer includes a surface off-cut at an angle in a range of from about 0.2 to about 8 degrees toward 11-20 or 10-10 from a c-plane of said single crystal III-V nitride material.
36. (Previously presented) A wafer comprising the material of claim 26, finished by a process including at least one of lapping, polishing and CMP.
37. (Previously presented) A wafer comprising the material of claim 26, finished by a process including CMP.

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38. (Previously presented) A wafer comprising the material of claim 26, having at least one surface with a DDSDR of less than 50%.
39. (Previously presented) A wafer comprising the material of claim 26, having at least one surface with a DDSDR of less than 25%.
40. (Previously presented) A wafer comprising the material of claim 26, having at least one surface with a DDSDR of less than 10%.
41. (Previously presented) A wafer comprising the material of claim 26, having at least one epitaxial layer thereon.
42. (Original) The wafer of claim 41, wherein said at least one epitaxial layer comprises a heteroepitaxial layer.
43. (Original) The wafer of claim 41, wherein said at least one epitaxial layer comprises a homoepitaxial layer.
44. (Previously presented) An electronic device article including a wafer comprising the material of claim 26, and an electronic device structure fabricated on said wafer.
45. (Original) The electronic device article of claim 44, wherein the electronic device structure includes a laser diode.
46. (Original) The electronic device article of claim 44, wherein the electronic device structure includes a light-emitting diode.
47. (Original) The electronic device article of claim 44, wherein the electronic device structure includes a high electron mobility transistor.
48. (Original) The electronic device article of claim 44, wherein the electronic device structure comprises integrated circuitry.
49. (Original) The electronic device article of claim 44, wherein the electronic device structure includes an opto-electronic device.

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50. (Original) Material according to claim 1, as grown under single crystal III-V nitride growth conditions slightly deviated from optimal single crystal III-V nitride growth conditions.

51. (Original) A wafer comprising material as claimed in claim 50.

52-120. (Cancelled).